

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows. Please cancel claims 21-23 without prejudice or disclaimer.

1. (Currently Amended) A method of forming a phase shift mask, said method comprising:

forming an opaque layer on a transparent substrate;

performing a first patterning of said opaque layer to expose a first region of said transparent substrate, wherein said first region comprises an uninterrupted rectangular surface shape;

etching said first region of said transparent substrate to create a phase shift region comprising an uninterrupted rectangular surface within said transparent substrate; and performing additional patterning of said opaque layer to expose a second region of said transparent substrate, ~~such that said second region comprises a similar shape and size as said first region, wherein said patterning includes said second region and first region, is vertically aligned with one side of said first region, and exposes an uninterrupted rectangular shape in said second region on said opaque layer immediately adjacent and substantially similar in shape and size to said first region, and~~

removing said opaque layer within said second region to create an uninterrupted rectangular surface on said transparent substrate,

~~wherein said second region is adjacent said first region, and~~

wherein said ~~additional patterning~~ process enlarges an opening in said opaque layer formed in said first patterning process.

2. (Canceled).

3. (Original) The method in claim 1, wherein said first region and said second region comprise a continuous area of said transparent substrate.

4. (Original) The method in claim 1, wherein said opaque layer comprises a chrome mask.

5. (Original) The method in claim 1, wherein said transparent substrate comprises a quartz substrate.

6-7. (Canceled).

8. (Currently Amended) A method of forming a phase shift mask, said method comprising:

forming an opaque layer on a transparent substrate;

performing a first patterning of said opaque layer to expose first regions of said transparent substrate, wherein said first regions comprise uninterrupted rectangular ~~surfaces~~ shapes;

etching said first regions of said transparent substrate to create phase shift regions comprising uninterrupted rectangular surfaces within said transparent substrate; and

performing additional patterning of said opaque layer to expose second regions and third regions of said transparent substrate, such that said patterning includes said second regions comprise similar shapes and sizes as said first regions, wherein said second regions are adjacent said first regions and said first regions, is vertically aligned with one side of said first regions, and exposes uninterrupted rectangular shapes in said second region on said opaque layer immediately adjacent and substantially similar in shape and size to said first regions, and said third regions are separated from said first regions, such that said third regions are devoid of phase shift features, and wherein said additional patterning process enlarges openings in said opaque layer formed in said first patterning process.

9. (Canceled).

10. (Original) The method in claim 8, wherein each pair of said first regions and said second regions comprises a continuous area of said transparent substrate.

11. (Original) The method in claim 8, wherein said opaque layer comprises a chrome mask.

12. (Original) The method in claim 8, wherein said transparent substrate comprises a quartz substrate.

13-14. (Canceled).

15. (Currently Amended) A method of forming a phase shift mask, said method

comprising:

forming an opaque chrome layer on a transparent quartz substrate;

performing a first patterning of said opaque chrome layer to expose a first region of said transparent quartz substrate, wherein said first region comprises an uninterrupted rectangular surface shape;

etching said first region of said transparent quartz substrate to create a phase shift region comprising an uninterrupted rectangular surface within said transparent quartz substrate; and

performing additional patterning of said opaque chrome layer to expose a second region of said transparent quartz substrate, ~~such that said second region comprises a similar shape and size as said first region, wherein said patterning includes said second region and first region, is vertically aligned with one side of said first region, and exposes an uninterrupted rectangular shape in said second region on said opaque layer immediately adjacent and substantially similar in shape and size to said first region, and~~

removing said opaque layer within said second region to create an uninterrupted rectangular surface on said transparent quartz substrate,

~~wherein said second region is adjacent said first region, and,~~

wherein said additional patterning process enlarges an opening in said opaque layer formed in said first patterning process.

16. (Canceled).

17. (Original) The method in claim 15, wherein said first region and said second region comprise a continuous area of said transparent quartz substrate.

18. (Original) The method in claim 15, wherein said opaque chrome layer comprises a chrome mask.

19-23. (Canceled).

24. (Previously Presented) The method in claim 1, wherein said uninterrupted rectangular surface lacks an intervening structure.

25. (Previously Presented) The method in claim 8, wherein said uninterrupted rectangular surfaces lack intervening structures.

26. (Previously Presented) The method in claim 15, wherein said uninterrupted rectangular surface lacks an intervening structure.